TC74AC125P/F/FN, TC74AC126P/F/FN

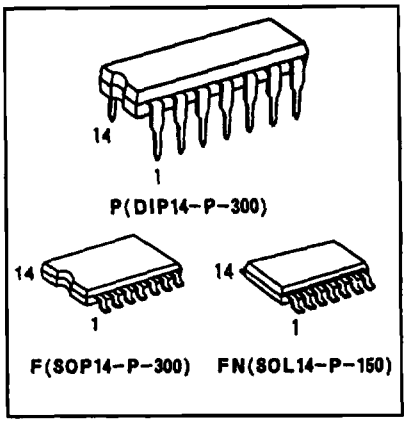
TC74AC125P/F/FN QUAD BUS BUFFER
TC74AC126P/F/FN QUAD BUS BUFFER

The TC74AC125/126 are advanced high speed CMOS QUAD BUS BUFFERs fabricated with silicon gate and double-layer metal wiring C²MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The TC74AC125 requires the 3-state control input $\overline{G}$ to be set high to place the output into the high impedance state, whereas the TC74AC126 requires the control input to be set low to place the output into high impedance.

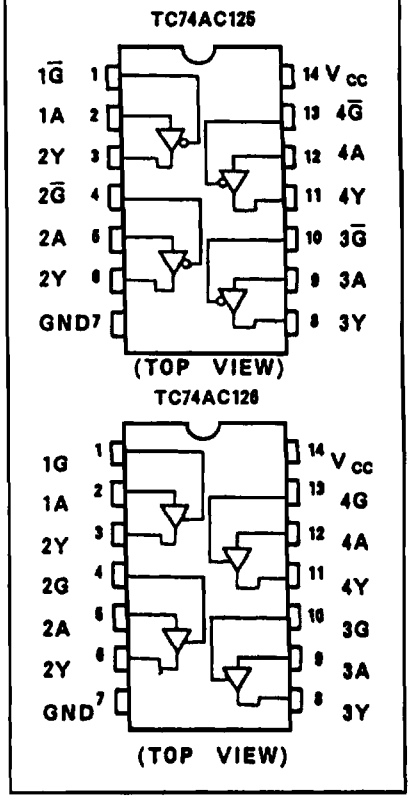
All inputs are equipped with protection circuits against static discharge or transient excess voltage.



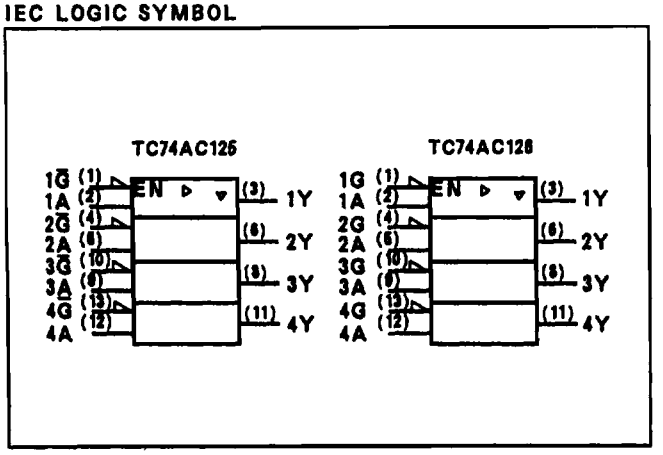
FEATURES:

- High Speed ..... t_{pd}=4.7ns(typ.) at V_{CC}=5V
- Low Power Dissipation ..... I_{CC}=8μA(Max.) at Ta=25℃
- High Noise Immunity ..... $V_{NIH}=V_{NIL}$=28% V_{CC}(Min.)
- Symmetrical Output Impedance ··· $|I_{OH}|=I_{OL}$=24mA(Min.)
  Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays ····· $t_{pLH} \simeq t_{pHL}$.
- Wide Operating Voltage Range ··· V_{CC}(opr)=2V~5.5V
- Pin and Function Compatible with 74F 125/126

PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

TC74AC125

INPUTS		OUTPUTS
$\overline{G}$	A	Y
H	X	Z
L	L	L
L	H	H

X : Don't Care
Z : High Impedance

TC74AC126

INPUTS		OUTPUTS
G	A	Y
L	X	Z
H	L	L
H	H	H

X : Don't Care
Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	−0.5 ~6.0	V
DC Input Voltage	V_{IN}	−0.5 ~V_{CC}+0.5	V
DC Output Voltage	V_{OUT}	−0.5 ~V_{CC}+0.5	V
Input Diode Current	I_{IK}	±20	mA
Output Diode Current	I_{OK}	±50	mA
DC Output Current	I_{OUT}	±50	mA
DC V_{CC}/Ground Current	I_{CC}	±100	mA
Power Dissipation	P_D	500(DIP)*/180(SOP)	mW
Storage Temperature	T_{stg}	−65 ~150	℃
Lead Temperature 10sec	T_L	300	℃

*500mW in the range of Ta= −40℃~ 65℃. From Ta=65℃ to 85℃ a derating factor of −10mW/℃ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2.0~5.5	V
Input Voltage	V_{IN}	0 ~ V_{CC}	V
Output Voltage	V_{OUT}	0 ~ V_{CC}	V
Operating Temperature	T_{opr}	−40 ~ 85	℃
Input Rise and Fall Time	dt/dv	0~100(V_{CC}=3.3±0.3V) 0~ 20(V_{CC}= 5 ±0.5V)	ns/v

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		V_{CC}	Ta=25℃ MIN.	Ta=25℃ TYP.	Ta=25℃ MAX.	Ta=−40~85℃ MIN.	Ta=−40~85℃ MAX.	UNIT
High-Level Input Voltage	V_{IH}			2.0 3.0 5.5	1.50 2.10 3.85	− − −	− − −	1.50 2.10 3.85	− − −	V
Low-Level Input Voltage	V_{IL}			2.0 3.0 5.5	− − −	− − −	0.50 0.90 1.65	− − −	0.50 0.90 1.65	V
High-Level Output Voltage	V_{OH}	V_{IN}= V_{IH} or V_{IL}	I_{OH}=−50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	− − −	1.9 2.9 4.4	− − −	V
			I_{OH}=−4mA I_{OH}=−24mA I_{OH}=−75mA*	3.0 4.5 5.5	2.58 3.94 −	− − −	− − −	2.48 3.80 3.85	− − −	
Low-Level Output Voltage	V_{OL}	V_{IN}= V_{IH} or V_{IL}	I_{OL}=50μA	2.0 3.0 4.5	− − −	0.0 0.0 0.0	0.1 0.1 0.1	− − −	0.1 0.1 0.1	V
			I_{OL}=12mA I_{OL}=24mA I_{OL}=75mA*	3.0 4.5 5.5	− − −	− − −	0.36 0.36 −	− − −	0.44 0.44 1.65	
3-State Output Off-State Current	I_{OZ}	V_{IN}=V_{IH} or V_{IL} V_{OUT}=V_{CC} or GND		5.5	−	−	±0.5	−	±5.0	μA
Input Leakage Current	I_{IN}	V_{IN}=V_{CC} or GND		5.5	−	−	±0.1	−	±1.0	
Quiescent Supply Current	I_{CC}	V_{IN}=V_{CC} or GND		5.5	−	−	8.0	−	80.0	

* :This spec indicates the capability of driving 50Ω transmission lines.
One output should be tested at a time for a 10ms maximum duration.

AC ELECTRICAL CHARACTERISTICS(C_L=50pF, R_L=500Ω, Input t_r=t_f=3ns)

PARAMETER	SYMBOL	TEST CONDITION		Ta=25℃			Ta=−40∼85℃		UNIT
			V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t_{pLH}		3.3±0.3	−	6.4	10.5	1.0	12.0	ns
	t_{pHL}		5.0±0.5	−	4.7	7.0	1.0	8.0	
Output Enable Time	t_{pZL}		3.3±0.3	−	7.1	12.3	1.0	14.0	
	t_{pZH}		5.0±0.5	−	5.0	7.9	1.0	9.0	
Output Disable Time	t_{pLZ}		3.3±0.3	−	5.1	8.8	1.0	10.0	
	t_{pHZ}		5.0±0.5	−	4.6	6.6	1.0	7.5	
Input Capacitance	C_{IN}			−	5	10	−	10	pF
Output Capacitance	C_{OUT}			−	10	−	−	−	
Power Dissipation Capacitance	C_{PD} (1)			−	24	−	−	−	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation:

$$I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{(per Gate)}$$